



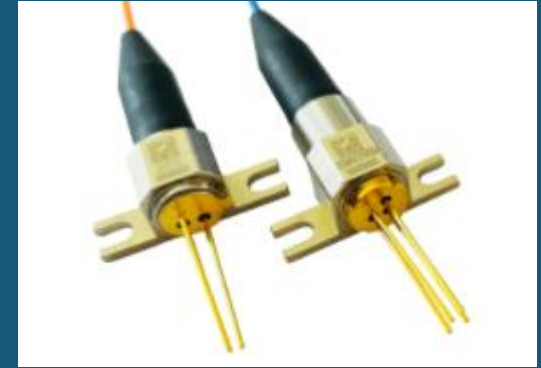
## CWDM (1270nm~1610nm) DFB Pulse laser diode module

### Features

- Advanced Multiple Quantum Well (MQW) laser
- Distributed Feedback (DFB) Laser Design
- Low Threshold Current
- Built-in InGaAsP monitor PD
- Cost-effective Uncooled Laser Technology
- 1 Pulse Conditions: Pulse width (PW)=10us, Duty = 1%

### Application

- CATV Return-Patch
- Analog Transmission
- Light Source
- Sensor
- Optical telecommunication
- OTDR



### Absolute Maximum Ratings (Tc=25°C .unless otherwise specified)

Parameter	Symbol	Min.	Max.	Unit	Test Condition
Reverse voltage ( monitor PD)	$V_{RM}$	-	10	V	-
Reverse Voltage	$V_R$		2	V	CW
Operating Temperature	$T_{OP}$	-20	+70	°C	-
Storage Temperature	$T_{stg}$	-40	+100	°C	-
Soldering Temperature/Time	-	260/10		°C/S	-

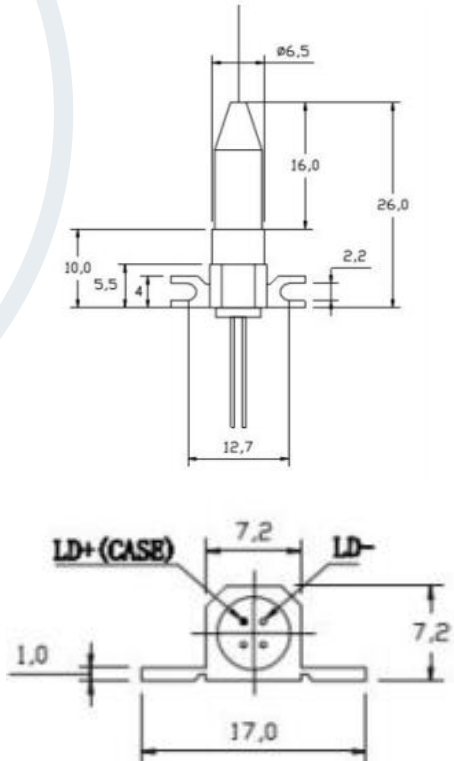


Reverse Current (monitor PD)	$I_{FPM}$	-	2	mA	-
Relative Humidity (non-condensing)	RH		85	%	-

## Optical & electrical characteristics (Tc=25°C)

Parameter	Symbol	Min	Typ.	Max.	Unit	Test Conditions
Optical Output Power	$P_o$	30	-	-	mW	IFP= 350mA, Pw=10us, Duty= 1%, 30s, min.
Threshold Current	$I_{th}$	0.05	-	2	mA	Pfcw = 2mW, Vrm = 2V
Forward Voltage	V <sub>F</sub>	-	-	3.5	V	IFP= 350mA, Pw=10us, Duty= 1%
Center Wavelength	$\lambda_c$	1290	1310	1330	nm	Rms (-20 dB ), IFP=350mA, Pw=10us, Duty= 1%
		1530	1550	1570		
		$\lambda_c-3$	$\lambda_c$	$\lambda_c+3$		
Spectral Width (-20 dB )	$\Delta \lambda$	-	0.5	1	nm	CW, 25°C, I <sub>th</sub> + 20mA
Rise / Fall time	Tr / Tf	-	0.3	0.7	ns	CW, I <sub>th</sub> + 20mA
Monitor Dark Current	ID	-	-	200	nA	Vrpd = 5 V
Optical Isolation	ISO	30	-	-	dB	25°C

## Dimensions(mm)



## Order Information

### GTA1003

“O Wavelength” 1270nm ~ 1410nm.

“S+C+L Wavelength” 1430nm ~ 1610nm.



Please let us know your request details before order.



Customize for you

